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G K PADAM & G L MALHOTRA (India), Preparation and study of CdTe thin films grown by the solution method.
D NAGLE, V R PAI VERNEKER, AN PETELIN & G GROFF (USA), Optical absorption of electrolytically colored single crystals of yttria-stabilized zirconia.
M BRAGLIA, M FERRARIS, G GREGO, G PARISI & F TAIARIOL (Italy), Different fluorination processes with ammonium bifluoride and their effect on fluorozirconate glasses.
A HAYASHI, T KISHI, Y UEDA & K KOSUGE (Japan), Phase diagram and magnetic properties of the $(Fe_xTi_{1-x})_3Se_4$ system.
H K HENISCH (USA), Threshold switching - a form of superconductivity?

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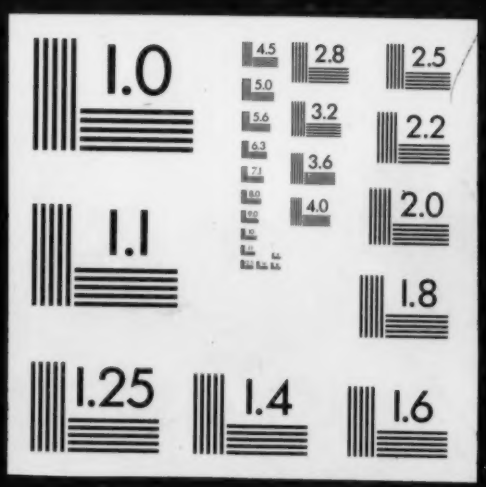
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